

INCHANGE SEMICONDUCTOR

isc Silicon NPN Darlington Power Transistor

2SD930

DESCRIPTION

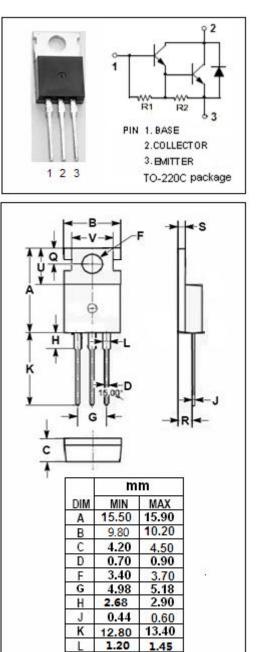
- High DC Current Gain
- : h_{FE}= 700(Min.)@ I_C= 1A, V_{CE}= 4V
- · High Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO} = 180V(Min)
- High Reliability
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Color & B/W TV power supply
- Active power filter
- Series regulators
- · General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------|
| V _{CBO} | Collector-Base Voltage | 200 | V |
| V _{CEO} | Collector-Emitter Voltage | 180 | V |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| Ic | Collector Current-Continuous | 5 | A |
| I _{CP} | Collector Current-Peak 8 | | A |
| I _B | Base Current-Continuous | 0.5 | А |
| Pc | Collector Power Dissipation @T _C =25°C | 30 | W |
| Tj | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature Range | -55~150 | °C |



isc website: www.iscsemi.com

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2.70

2.30

1.29

6.45

8.66

2.90

2.70

1.35

6.65

8.86



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|--|-----|------|-------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA, I _B = 0 | 180 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _B = 0 | 200 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 3mA; I _C = 0 | 6 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1.5A ,I _B = 50mA | | | 1.5 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 1.5A ,I _B = 50mA | | | 2.0 | V |
| Ісво | Collector Cutoff current | V _{CB} = 200V, I _E = 0 | | | 0.1 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 180V, I _B = 0 | | | 0.5 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 3 | mA |
| hfe | DC Current Gain | I _C = 1A ; V _{CE} = 4V | 700 | | 20000 | |

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